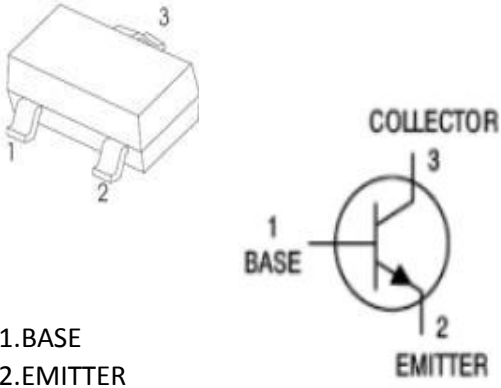


TRANSISTOR (PNP)	SOT-23 Plastic-Encapsulate Transistors		
<p><u>SOT-23</u></p>  <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :2T1</p>	<p>Features</p> <ul style="list-style-type: none"> ※ Complimentary to S9013 ※ Collector Current: $I_c=0.5A$ ※ Excellent Hfe Linearity 		
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-40	V
Collector-Emitter Voltage	VCEO	-25	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RθJA	417	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

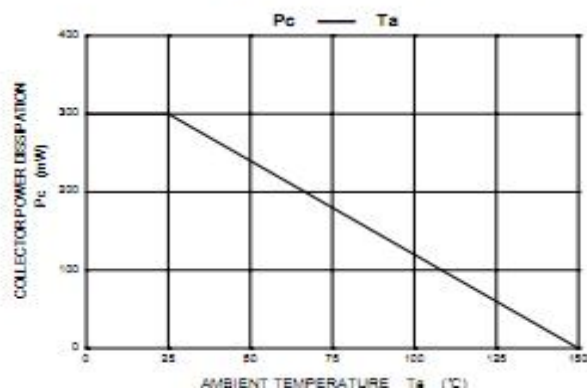
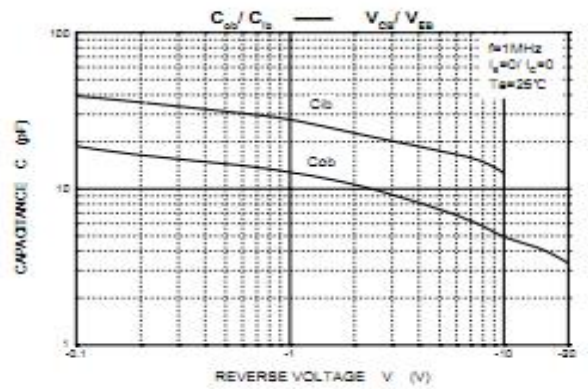
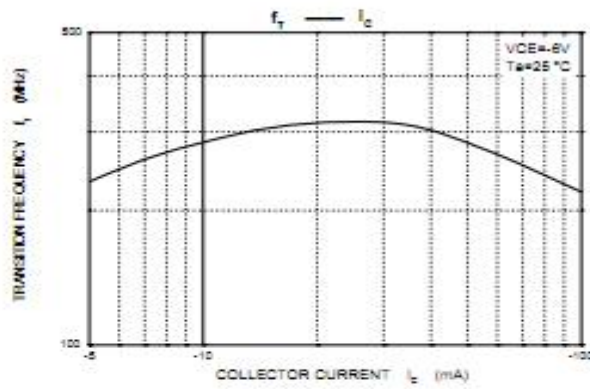
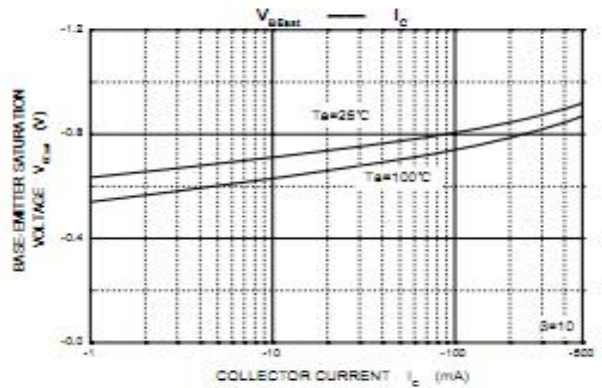
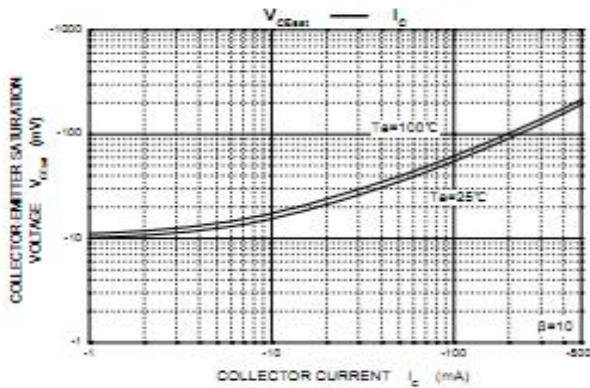
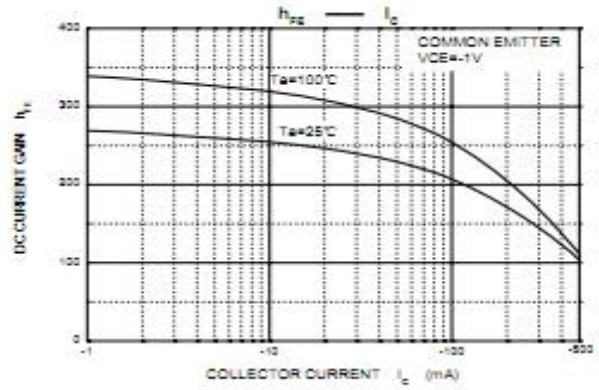
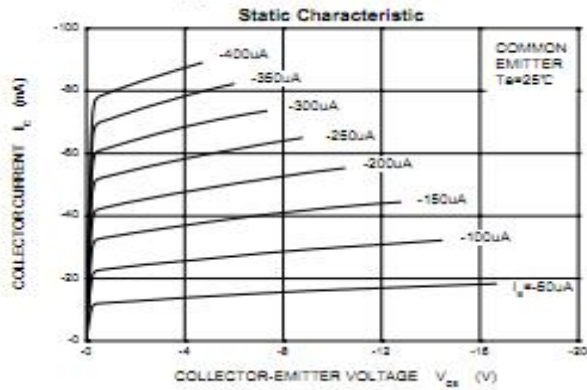
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100 μ A, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100 μ A, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-40 V , IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCB=-25V , IE=0			-0.1	μ A
Emitter cut-off current	IEBO	VEB= -5V , IC=0			-0.1	μ A
DC current gain	hFE	VCE=-1V, IC= -50mA	120		400	
	hFE	VCE=-1V, IC= -500mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=-500 mA, IB= -50mA			-0.6	V
Base-emitter saturation voltage	VBE(sat)	IC=-500 mA, IB= -50mA			-1.2	V
Transition frequency	fT	VCE=-6V, IC= -20mA f=30MHz	150			MHz

CLASSIFICATION OF hFI

Rank	L	H	J
Range	120-200	200-350	300-400

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)